

Applicant(s): Ricky Amos, et al.

Examiner: Matthew C. Landau

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For: HIGH TEMPERATURE PROCESSING
COMPATIBLE METAL GATE ELECTRODE
FOR pFETs AND METHOD FOR FABRICATION

Confirmation No: 9669

Exhibit B

1. Describe your invention, stating the problem solved (if appropriate), and indicating the advantages of using the invention.

The invention is the fabrication of a CMOS gate electrode comprising a Re, Rh, Pt, Ir or Ru metal. The work functions of Re, Rh, Pt, Ir or Ru make them compatible with current pFET requirements. The

requirements of the pFET gate material along with experimental results are described below. The requirements are divided into four sections physical characterization, deposition techniques, electrical characterization and integration.

Physical characterization - Depending on the integration scheme thermal stability (preferably up to 1000 C) from agglomeration, from reaction with the dielectric (formation of an interlayer between the gate metal and dielectric) and reaction with the annealing ambient (forming gas (FG) or hydrogen (H)) is required of the metal gate material. A second requirement is low resistivity, 1-2 mOhm-cm for the gate contact and more preferably lower than 50 micro Ohm-cm for gate contact plus local interconnect use (like what is currently practiced with silicides). Rhenium has a resistivity lower than 50 micro Ohm-cm after a 1000 C FG anneal treatment on both SiO₂ and Al₂O₃ dielectrics.

The thermal stability of various gate materials in contact with both SiO₂ and Al₂O₃ dielectrics were investigated using three techniques employed at the Brookhaven National Laboratory, National Synchrotron Light Source. The techniques include time resolved x-ray diffraction analysis used to determine if the metal electrode undergoes an interaction with the dielectric layer or FG annealing ambient, optical scattering and resistance analysis as a function of temperature used to determine if the film undergoes agglomeration or thermal degradation. All three techniques were monitored simultaneously while the samples were heated from 100 to 1000 C in FG. It was determined that for the stack of 30 nm Re, Rh, Pt or Ir on 500 nm SiO₂ or 300 nm Al₂O₃ there was no thermal degradation or reactions during the anneal treatments. The two graphs below show the results from the 50 nm CVD Re / 500 nm SiO₂ and 30 nm PVD Re / 300 nm Al₂O₃ stacks annealed to 1000 C in FG.

Figure 1 below shows the results from annealing a 50 nm CVD Re film on 500 nm SiO₂ in FG at 3 C/s up to 1000 C. The contour plot (diffraction angle vs. temperature with color scale indicating x-ray intensity, dark blue lowest intensity and dark red highest intensity) follows the (002) orientation of Re as a function of temperature. Notice the peak linearly moves to lower angles on annealing due to lattice expansion and at about 750 C the intensity increases indicating grain growth in the film. There are no indications of additional peaks or a decrease in intensity of the (002) peak which would signify a reaction with the dielectric or annealing ambient. The top plot shows the optical scattering analysis at two different lateral length scales (0.5 and 5 micro meters, red and blue curves respectively). Changes would indicate surface roughness developing in the film leading to thermal degradation. In this case no changes are seen indicating the film is not agglomerating.

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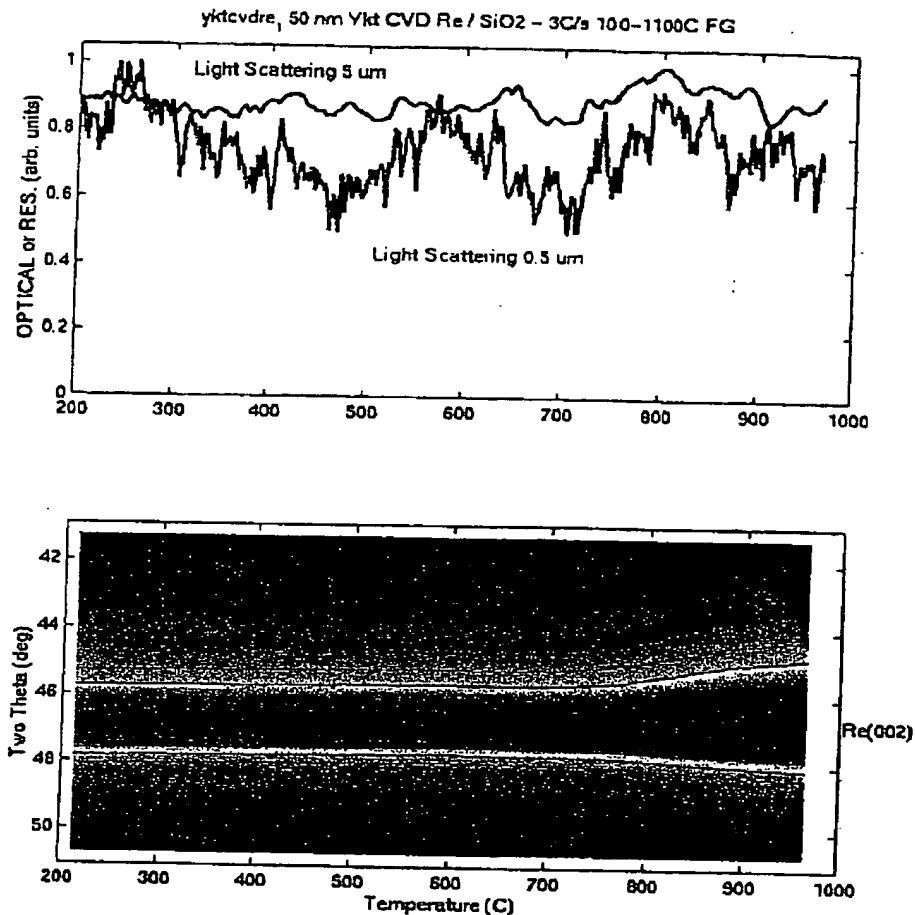


Figure 1

Figure 2 shows the results from annealing a 30 nm PVD Re film on 300 nm Al₂O₃ in FG at 3 C/s up to 1000 C. The contour plot (diffraction angle vs. temperature with color scale indicating x-ray intensity, dark blue lowest intensity and dark red highest intensity) follows the (002) orientation of Re as a function of temperature. Notice the peak linearly moves to lower angles on annealing due to lattice expansion. There are no indications of additional peaks or a decrease in intensity of the (002) peak which would signify a reaction with the dielectric or annealing ambient. The top plot shows the optical scattering analysis at two different lateral length scales (0.5 and 5 micro meters, red and blue curves respectively). Changes would indicate surface roughness developing in the film leading to thermal degradation. In this case no changes are seen indicating the film is not agglomerating. The black curve shows sheet resistance as a function of temperature. The initial decrease indicates some grain growth in the layer.

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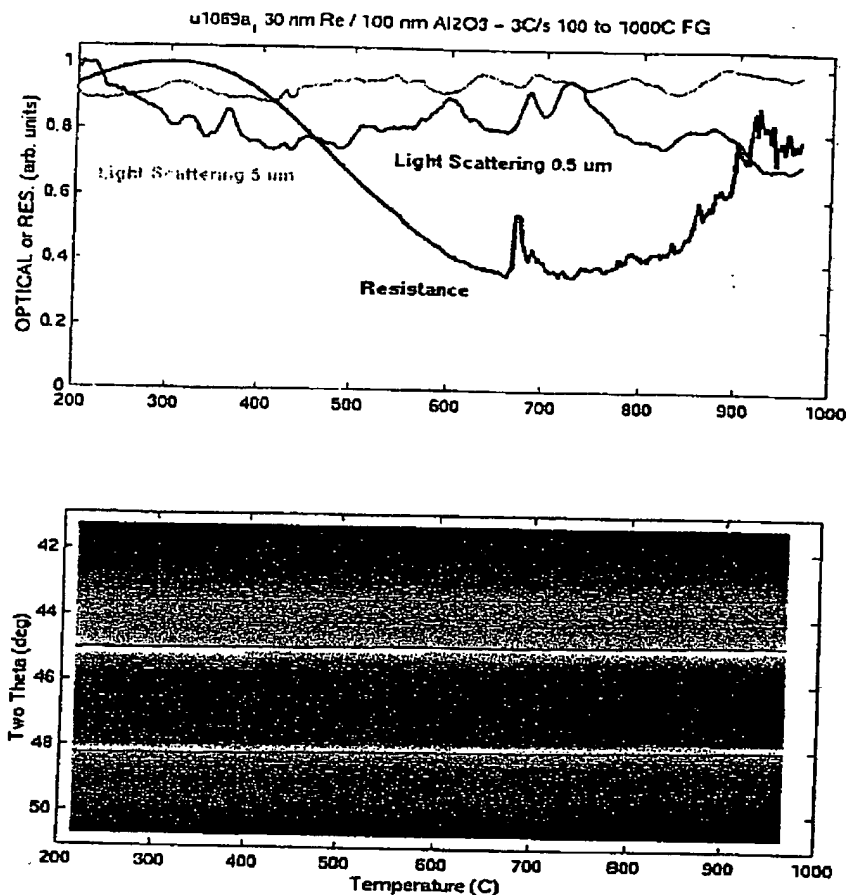


Figure 2

The time resolved techniques employed at the Brookhaven National Laboratory did not show any indication of thermal degradation or reactions for the Re, Rh, Pt and Ir gate materials in contact with SiO₂ or Al₂O₃. The time resolved x-ray diffraction technique would only be sensitive to a reaction between the gate metal and dielectric which forms an interlayer greater than about 4-5 nm in thickness. As a finer check to determine if there was an interaction at the interface, x-ray reflectivity analysis was used. With this technique, also conducted at the Brookhaven National Laboratory, we are able to see roughness changes at the metal - dielectric interface on the order of a few angstrom's which would indicate and interaction. The technique also allows us to determine the thickness of the layers present and in that manner we can monitor if the dielectric layer gets thinner or if a third interlayer forms which would again indicate an interaction between the metal and dielectric. A further result this technique provides is an indication of the surface roughness of the films. Table 1 below summarizes the results. The first thing to note is that as-deposited the CVD Re films have a 6-7 times higher surface roughness. After a 450 C / 30 min. FG anneal treatment the interface roughness of the Re, Rh and Ir samples increases only slightly indicating very little interaction between the metal and dielectric. The Pt film actually became smoother after the FG anneal treatment. For the Re films on both SiO₂ and Al₂O₃ there was no change in the dielectric thickness after the FG anneal treatment. These results again confirm that there is no interaction between Re, Rh, Pt and Ir gate metal materials and the dielectric after a 450 C FG anneal

treatment. As an example of interlayer formation, if titanium, a very reactive material, is used as the gate metal, after the FG anneal treatment, an interlayer is clearly seen indicating a reaction between the metal and dielectric.

X-ray Reflectivity Measurements of Metal Gate and Gate Oxide Materials

Surface Roughness

Interface Roughness

Material	as dep.	after anneal (FG 450 C / 30 min.)	comments
CVD Re / SiO ₂	$\sigma \sim 30-40$ Å	Re slightly rougher	no change in SiO ₂ thickness
PVD Re / SiO ₂	$\sigma \sim 7$ Å	Re slightly rougher	no change in SiO ₂ thickness
CVD Re / Al ₂ O ₃	$\sigma \sim 43-49$ Å	Re slightly rougher	no change in Al ₂ O ₃ thickness
PVD Re/Al ₂ O ₃	$\sigma \sim 8-9$ Å	Re slightly rougher	no change in Al ₂ O ₃ thickness
PVD Rh / SiO ₂		Rh slightly rougher	
Ir / SiO ₂		Ir slightly rougher	
Pt / SiO ₂		Pt slightly smoother	

Table 1

Figure 3 shows that PVD 30 nm films of Re, Rh, Pt and Ir after undergoing various thermal treatments (annealing in FG at 3 C/s to 450, 550, 750 and 1000 C) maintain resistivities below 50 micro Ohm-cm. The plot on the left shows the results for films deposited on 500 nm SiO₂ and that on the right on a 300 nm Al₂O₃ dielectric. These results indicate that the films are thermally stable and can be used in a standard high temperature integration scheme not only as the gate contact but also as local interconnects.

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Resistivity of Thermally Stable Metal Gate Materials for pFET Contacts

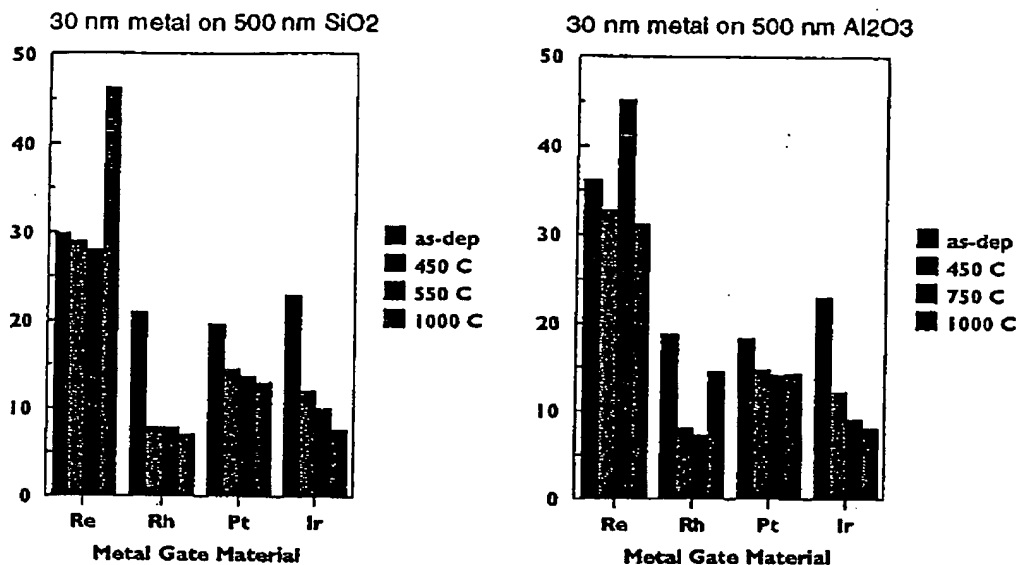


Figure 3

The CVD deposited Re films on SiO₂ show strong 0002 texture as shown in Fig. 4 with an x-ray diffraction analysis. The textured films were observed independent of growth temperature for films with thicknesses less than 100 nm. The top plot in Fig. 4 shows a standard theta / two theta x-ray diffraction diffractogram which indicates the strong 0002 textured peak at about 40 deg. two theta. The lower plot shows a chi scan (fiber plot) further indicating the textured nature of the film.

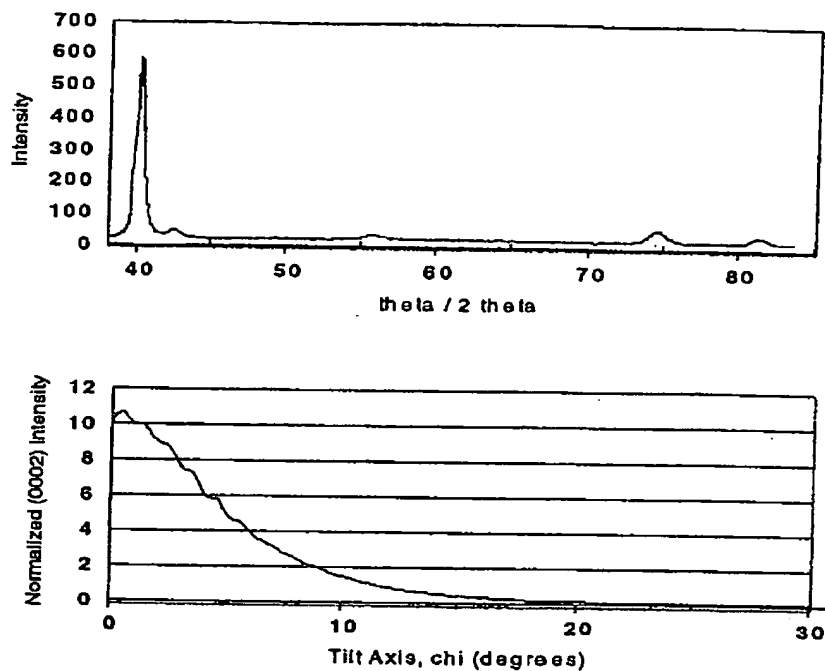


Figure 4

Deposition techniques - Acceptable deposition processes which lead to minimal gate dielectric damage and minimal long term reliability problems include thermal evaporation (from Knudsen cells) and chemical vapor deposition (CVD). Other PVD processes such as sputtering and e-beam evaporation lead to dielectric damage which is thought to be a long term reliability problem even if some damage may be repaired by a FG or H anneal treatment. CVD has the advantage over thermal evaporation in that it can be used to fill higher aspect ratio damascene features allowing for a wider variety of integration schemes. A Re CVD process has been developed using a dirhenium decacarbonyl, $\text{Re}_2(\text{CO})_{10}$, precursor.

It is emphasized that the deposition of Re using CVD techniques is already known in the art. However, the deposited Re films using halide precursor causes problems of halogen incorporation and the growth temperature was usually high and the previous attempt to grow using $\text{HRe}(\text{CO})_5$ resulted in films with high carbon concentrations. Another attempt using $\text{Re}_2(\text{CO})_{10}$ was done at high temperature about 500 °C and the properties of films were untested.

Despite the potential use of rhenium carbonyl in wiring applications, there is no disclosure of using $\text{Re}_2(\text{CO})_{10}$ as the CVD source material for providing p-channel Re gates on dielectric materials such as ultra-thin gate dielectric materials.

The Re electrode fabrications in the current invention are achieved by using a low temperature/low pressure CVD technique with $\text{Re}_2(\text{CO})_{10}$ as the source material. Specifically, the method of the present invention comprises the steps of: (a) depositing a uniform layer of Re directly onto a dielectric material such as an ultra-thin gate dielectric material, said dielectric material being positioned on a semiconductor substrate, said deposition is carried out by CVD using $\text{Re}_2(\text{CO})_{10}$ as the source material under conditions which are sufficient to form said Re layer; and (b) patterning the structure formed in step (a) using simple patterning process including Al deposition and selective wet etching of the

structure or standard lithographic techniques to form a test capacitors or MOS device containing said p-channel Re gate on said dielectric material. It is emphasized that no chemical activation step is required in the present invention to deposit the Re layer onto the dielectric material. The present invention also provides MOS devices such as FETs which comprise at least one p-channel Re gate prepared in accordance with the method of the present invention. The devices of the present invention exhibit gate leakage comparable to prior devices prepared in accordance with existing technology and they exhibit the theoretical value for metal-gate workfunction. In accordance with this embodiment of the present invention, the Re electrode is fabricated by a method which comprises the steps of: (a) depositing a layer of Re onto a dielectric material, wherein said deposition is carried out by chemical vapor deposition (CVD) using $\text{Re}_2(\text{CO})_{10}$ as a source material; (b) patterning said Re layer to form said Re electrode on said dielectric material; and (c) passivating Re and dielectric materials using conventional forming gas annealing or high pressure hydrogen to produce very low interface charge density device structure.

The present invention provides a method of fabricating p-channel Re gates directly onto dielectric materials which are present on MOS devices. The p-channel Re gates produced in accordance with the present method are compatible with ultra-thin gate dielectric materials found on MOS devices and have resistivity values close to the ideal bulk value.

In accordance with the method of the present invention, a layer of Re is directly deposited on the surface of a dielectric material which is on top of a semiconductor substrate by employing CVD using $\text{Re}_2(\text{CO})_{10}$ as the source material under conditions which are sufficient to form Re layer on the dielectric material. That structure containing the Re layer is then patterned using conventional techniques well known to those skilled in the art.

The CVD apparatus includes a load-lock stainless steel reactor which comprises a graphite sample holder cartridge. The reactor further includes a boron nitride heater assembly for heating the sample during deposition and two ultra-high vacuum turbo-molecular pumps for controlling the pressure during the deposition providing base pressure of 10^{-7} torr.

The source material, dirhenium decacarbonyl, $\text{Re}_2(\text{CO})_{10}$, is introduced into reactor chamber via a stainless steel valve and is directed to a test wafer which is contained within reactor. The source material, $\text{Re}_2(\text{CO})_{10}$, which is white solid, is contained in glass tube and maintained at a constant temperature ranging from 20 to 70 °C during he deposition. The precursor is delivered by using Ar as carrier gas and the chamber pressure during growth is controlled by flow of Ar carrier gas.

CVD of $\text{Re}_2(\text{CO})_{10}$ occurs at a temperature of from about 300 °C to about 550 °C. More preferably, the CVD deposition of Re occurs at a temperature of from about 350° C to about 450 °C. The pressure of the reactor during CVD is about 3×10^{-2} Torr. The CVD process typically is carried out for a time period of from about 10 minutes to about 5 hrs. Higher deposition rate can be achieved by using higher precursor temperature and higher carrier gas flow.

It is noted that under the above conditions a layer of Re having a thickness of from about 2 to about 200 nm, more preferably from about 20 to about 100 nm is deposited directly onto the dielectric material.

The ultra-thin dielectrics materials employed in the present invention include SiO_2 , nitrided SiO_2 , Si_3N_4 , metal oxides and mixtures or combinations thereof. The dielectrics employed in the present invention may be grown, deposited or reacted by using techniques well known to those skilled in the art. Of the gate dielectric materials mentioned hereinabove, SiO_2 , lightly nitrided SiO_2 (5% or less total nitride content), Al_2O_3 , HfO_2 , or ZrO_2 is highly preferred at present.

After depositing the Re layer, the samples are patterned using Al as hard masks or standard lithographic techniques well known to those skilled in this art. This includes positioning photoresists on the surface of the CVD Re layer; developing the photoresists and removing, via etching techniques, those areas that do not contain the photoresists. Etching may be carried out using wet or dry techniques well known to those skilled in the art. When wet etching is employed, the chemical etchant is selected from the group consisting of H_2O_2 , chromic acid, phosphoric acid, acetic acid, and the like thereof. The preferred chemical etchant employed in the present invention is H_2O_2 . When dry chemical etching is employed in the present invention, it may be carried out by reactive ion etching (RIE), ion beam etching (IBE) or laser ablation. Each of the aforementioned dry etching techniques are well known to those skilled in the art.

Test structures were fabricated using thermally grown silicon dioxide thin films ranging in

thicknesses from 2.0-20.0 nm to form MOS capacitors. Additional experiments were performed on device structure wafers containing dielectric thickness from 1 to 2 nm and on Al₂O₃ layers grown by molecular beam epitaxy. Films were grown on p-type or n-type wafers with resistivities of about 0.1 to 0.2 ohm-cm. Re films were deposited on the test wafers in blanket fashion. Specifically, Re deposition was carried out in a load-locked, stainless steel reactor with a base pressure of about 10⁻⁷ torr. Dirhenium decacarbonyl, Re₂(CO)₁₀, was used as the source gas and it was emitted into the reactor via a stainless steel valve and directed onto the sample. The precursor delivery rate was controlled by using Ar as carrier gas. The samples were introduced on a graphite sample holder cartridge which in turn was introduced into a heater assembly located within the reactor chamber. The deposition was conducted at a temperature range of 300-550 °C. The growth rate in the system was typically about 0.1 to 1.5 nm/minute depending on precursor and deposition temperature.

Electrical characterization - For a gate metal pFET contact a work function within -0.2 eV from the valance band edge (Ev) is necessary. The work function for the Re metal gate material was established to be 4.6 to 5.0 eV. Besides the work function another important consideration is the interface trapped charge which can be minimized after deposition by a hydrogen anneal treatment. The conventional treatment is a FG anneal but a new process using 400 Torr of Hydrogen and 350 C has shown superior results. For the Re gate metal the interface trapped charge (Dit) was reduced to 3-4 E 10 /cm² * eV⁻¹ with the use of high hydrogen pressures necessary to produce properly passivated interfaces without the material undergoing chemical changes.

After deposition of the Re films, capacitors were patterned using evaporated 60 nm thick Al dots as hard mask for wet etching. The rhenium film on each device was wet-etched using H₂O₂. Capacitor structures were thus formed with areas ranging from about 1 E -6 to about 1 E -2 cm². Additionally, Re films were patterned by wet etching using standard lithography techniques for device structure wafers.

The capacitors prepared above were tested using high frequency and quasi-static capacitance-voltage (C-V) and current-voltage (I-V) techniques. FIG. 5 show typical C-V data for Re gate capacitors structures formed having a thickness of about 4.3 nm capacitor. Data is shown for capacitor formed on n-type silicon wafers. The dotted and solid lines show the C-V data before and after a standard post metal gate deposition forming gas anneal (FGA) step which is carried out in 10% H in nitrogen at 400 °C for about 30 minutes.

Analysis of the C-V data show interface state densities in the low 3-4 E 11 cm⁻²eV⁻¹ for samples subjected to FGA. The flat band voltage is approximately 0.5 eV. This, in itself, demonstrate that the Fermi-level of the metal gate is situated very close to silicon valence band edge indicating that Re gate is appropriate choice for p-FET MOS structure. The as-dep sample has some defects state as seen in FIG. 5 but can be easily removed by standard FGA step. C-V data were obtained for other Re gate capacitors with dielectric thickness ranging from 2-20 nm and the work function was evaluated as 5.0 eV.

Although the conventional FGA produces acceptable range of interface state density, it can be even improved by using newly developed high pressure H₂ annealing process. The process is performed in the load lock chamber using a He lamp heater. The patterned samples are located in the chamber and maintained at 350 °C and high pressure H₂ is introduced, typically 400 Torr for 30 minutes. By this process, the interface state densities are reduced to low (3-4) E 10 cm⁻²*eV⁻¹. FIG 6 shows typical high frequency and quasi-static C-V data for Re gate capacitors structures having an oxide thickness of about 20 nm capacitor after the high pressure annealing process.

C-V and I-V data for device structure wafers employing Re gates having oxide thickness of 2 nm are shown in FIGS. 7 and 8. The dotted and solid lines show the C-V and I-V data before and after a standard FGA step. These data demonstrates that the Re gate capacitors work on thin 2 nm gate dielectrics and have leakage currents as low as those of standard polysilicon based capacitors.

FIG 9 shows C-V data for Re gate capacitors structures formed on Al₂O₃ dielectrics having a thickness of about 6 nm. The capacitor is formed on an n-type silicon wafer. The flat band voltage was about 0.48 eV, which is essentially the same as on SiO₂. This indicates the Re can be used as electrode material for p-channel metal gates using Al₂O₃ as dielectric.

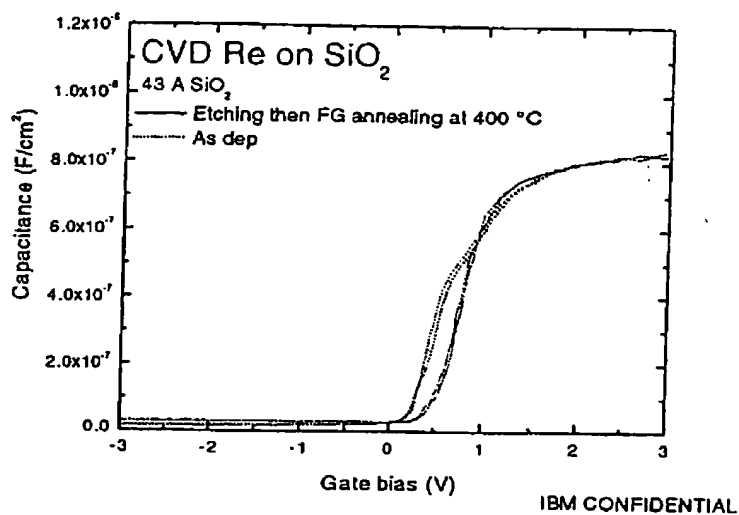


FIG. 5 is a capacitance-voltage diagram for a Re gate capacitor structure formed in accordance with the present invention having a thickness of 4.3 nm. Dotted line as grown; solid line after FGA.

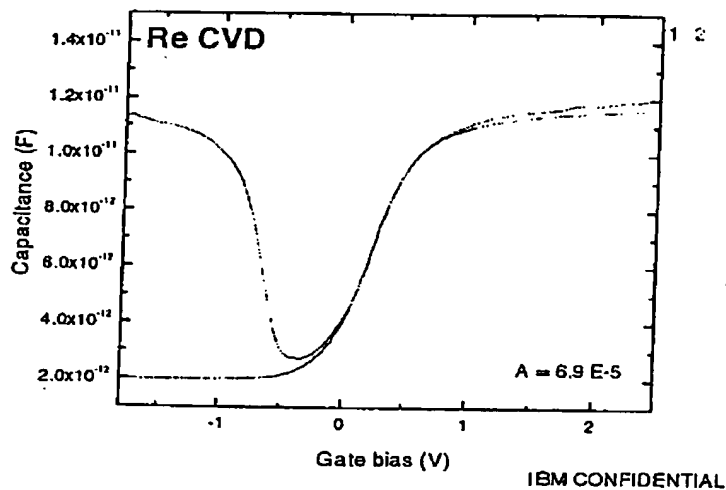


FIG. 6 is a high frequency and quasi-static capacitance-voltage diagram for a Re gate capacitor structure formed in accordance with the present invention having a thickness of 20 nm after high pressure H₂ annealing.

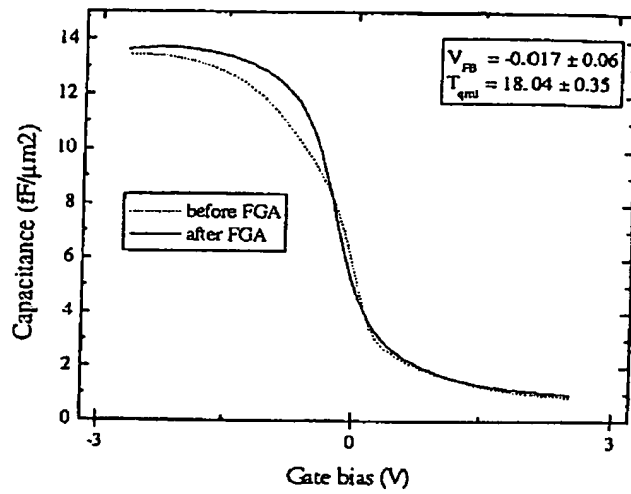


FIG. 7 is a high frequency capacitance-voltage diagram for a Re gate device structure formed in accordance with the present invention having a thickness of 2.0 nm. Dotted line as grown; solid line after FGA.

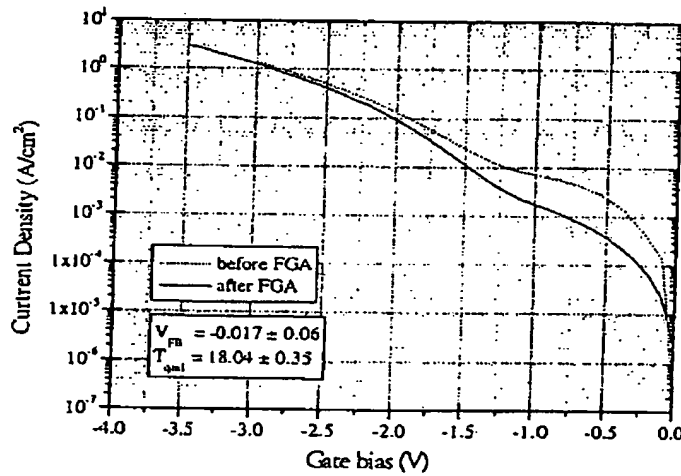


FIG 8 is a current-voltage diagram for a Re gate device structure formed in accordance with the present invention having a thickness of 2.0 nm. Dotted line as grown; solid line after FGA.

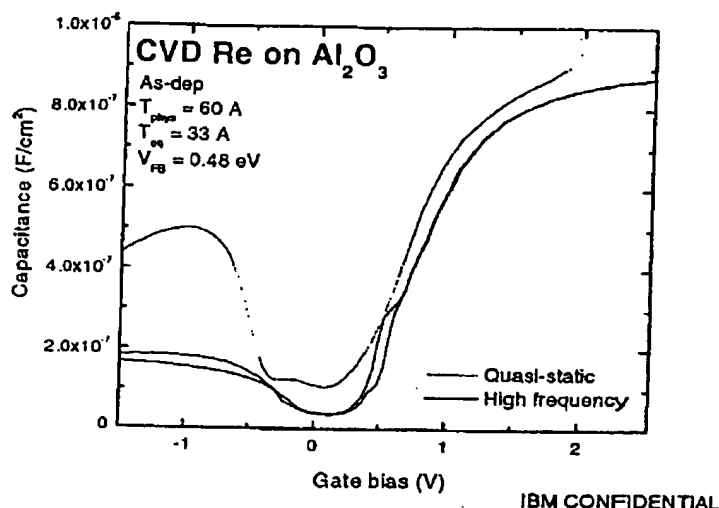


FIG. 9 is a high frequency and quasi-static capacitance-voltage diagram for a Re gate capacitor structure formed in accordance with the present invention on Al₂O₃ film having a thickness of 6 nm after FGA.

Integration - The integration scheme chosen will determine the maximum temperature the gate metal / dielectric will have to withstand. For a standard CMOS process for which the dielectric and poly-Si contact are in place before the source and drain activation anneals the stack will have to withstand 1000 C thermal treatments. As mentioned above Re, Rh, Pt, Ir and Ru can withstand such treatments without thermal degradation. Two additional possible integration schemes include having the metal / dielectric combination in place before source and drain silicide formation but not before the activation anneals. In this case the combination would have to withstand anneal treatments at 750 C for CoSi₂ formation. In the last integration scheme the standard process is followed (i.e. poly-Si flow). After the stack is built the poly-Si is etched away and the dielectric deposited followed by the metal fill (CVD process) into the damascene feature. Chemical mechanical polishing (CMP) is then used to planarize the structure. In this scheme the maximum processing temperature is 400 C.

Sample Claims

Device:

- 1) A MOS device comprising at least one pFET work-function material (Re, Rh, Ir, Pt, Ru) gate on an ultra thin dielectric material, said ultra-thin dielectric material having the primary gate leakage current due to direct tunneling, wherein said pFET work-function material is formed by
 - (a) depositing a layer of the pFET work-function material onto said ultra-thin gate dielectric material, said ultra-thin gate dielectric material being positioned on a semiconductor substrate and said deposition process being carried out by chemical vapor deposition (CVD) using (Re₂(CO)₁₀) as a source material;
 - (b) patterning the structure formed in step (a).
- 2) A field effect transistor (FET) comprising at least one pFET work-function material (Re, Rh, Ir, Pt, Ru) gate on an ultra thin dielectric material, said ultra-thin dielectric material having the primary gate leakage current due to direct tunneling, wherein said pFET work-function material is formed by
 - (a) depositing a layer of the pFET work-function material onto said ultra-thin gate dielectric material, said ultra-thin gate dielectric material being positioned on a semiconductor substrate and said deposition process being carried out by chemical vapor deposition (CVD) using (Re₂(CO)₁₀) as a source material;

- (b) patterning the structure formed in step (a).
- 3) The MOS device of claim one wherein said ultra-thin gate dielectric material is selected from the group consisting of SiO₂, nitrided SiO₂, Si₃N₄, metal oxides and mixtures thereof.
- 4) The MOS device of claim one wherein said ultra-thin gate dielectric material is selected from the group consisting of Al₂O₃, HfO₂, ZrO₃, Si₃N₄ and mixtures thereof.
- 5) The MOS device of claim three wherein said ultra-thin dielectric is SiO₂.
- 6) The MOS device of claim one wherein said semiconductor substrate contains at least one source and drain region.
- 7) The MOS device of claim six wherein said semiconductor substrate is p-type or n-type.
- 8) The MOS device of claim seven wherein said semiconductor substrate is composed of silicon, SiGe, SOI or GaAs.
- 9) The MOS device in claim eight wherein said semiconductor substrate is silicon.
- 10) The FET device of claim two wherein said ultra-thin gate dielectric material is selected from the group consisting of SiO₂, nitrided SiO₂, Si₃N₄, metal oxides and mixtures thereof.
- 11) The FET device of claim two wherein said ultra-thin gate dielectric material is selected from the group consisting of Al₂O₃, HfO₂, ZrO₃, Si₃N₄ and mixtures thereof.
- 12) The FET device of claim ten wherein said ultra-thin dielectric is SiO₂.
- 13) The MOS device of claim two wherein said semiconductor substrate contains at least one source and drain region.
- 14) The MOS device of claim thirteen wherein said semiconductor substrate is p-type or n-type.
- 15) The MOS device of claim fourteen wherein said semiconductor substrate is composed of silicon, SiGe, SOI or GaAs.
- 16) The MOS device in claim fifteen wherein said semiconductor substrate is silicon.

Method:

- 1) Method for forming at least one pFET Re, Rh, Pt, Ir or Ru metal contact in a semiconductor device comprising the following:
- a) positioning a preprocessed semiconductor substrate in a chemical vapor deposition chamber;
 - b) depositing a uniform layer of Re directly onto a dielectric material such as an ultra-thin gate dielectric, said ultra-thin dielectric material having the primary gate leakage current due to direct tunneling, said dielectric material being positioned on a semiconducting substrate, said deposition is carried out by CVD using Re₂(Co)₁₀ as the source material under conditions which are sufficient to form said Re layer;
 - c) patterning said Re layer to form said Re electrode on said dielectric material;
 - d) passivating said Re and dielectric materials using conventional forming gas annealing or high pressure hydrogen process to produce low interface charge density device structure.
2. How does the invention solve the problem or achieve an advantage, (a description of "the invention", including figures in-line as appropriate)?

The new pFET material solves two issues. The first is polycrystalline silicon depletion which reduces the effective capacitance of poly-Si gate devices, and necessitates the use of a thinner dielectric than would otherwise be required. The depletion in the poly-Si can be thought of as adding several angstrom's of oxide thickness to the dielectric. The second issue is the compatibility with high-k dielectrics (Al₂O₃, HfO₂, ZrO₂). Poly-Si tends to react with the high-k materials during processing which renders it unusable. The metal gate materials overcome this problem being stable on the high-k dielectric materials. The thermal stability (no interaction with the dielectric) makes it fully compatible with standard post processing techniques, e.g. activation anneals and the like.

3. If the same advantage or problem has been identified by others (inside/outside IBM), how have those others solved it and does your solution differ and why is it better?

The problem is generally known, but there are no fully satisfactory solutions extant.

4. If the invention is implemented in a product or prototype, include technical details, purpose, disclosure details to others and the date of that implementation.

N/A